## Early 1990s i-line reduction-projection exposure system

## ~ Discrete Semiconductor/Others ~

The g-line reduction- projection exposure (stepper) system became the standard for lithography in the 1.3 µm generation <sup>(1)</sup>. Since the resolution (R) of the stepper depended on the wavelength and NA (R  $\propto \lambda$  / NA), it was necessary to shorten the wavelength of the light source or increase the NA of the lens for lithography in the submicron region. The i-line (spectral line: 365 nm), which had a shorter wavelength than the g-line (spectral line: 436 nm), was used as a light source. In 1986, GCA commercialized an i-line stepper (NA=0.35) that resolves 0.7µm (8500DSW). Nikon had developed an i-line stepper (NSR-1010i3) with a resolution of 0.8µm in 1984 However, there was still no photoresist with high sensitivity for i-line, and Nikon and Canon tried to achieve high NA with g-line for 0.8µm. In the 0.8µm generation, g-line steppers became the mainstream.

Photoresist for i-line was developed by NAGASE at the end of the 1980s, and the development of reduction- projection exposure (stepper) of i-line began for the 0.5  $\mu$ m process in the 1990s. Nikon launched an i-line stepper (NA=0.5) with a resolution of 0.5  $\mu$ m (NSR-1755i7) in 1990. (Figure 1) Canon also developed the i-line stepper (FPA-2000i1). The i-line stepper became a main equipment of the VLSI industry for fabricating the 16M DRAM generation products with 0.5 $\mu$ m process. The i-line stepper continued to be upgraded in NA, and the resolution was improved to 0.35  $\mu$ m by Nikon and Canon in 1996, and it was also used for the production of the 64M DRAM generation.



Figure 1 i-line stepper (NSR-1755i7) (Courtesy of NIKON CORPORATION)

References:

[1] Semiconductor Museum of Japan, Process Technology, "Early 1980s: Advancing miniaturization requires the use of steppers in lithography" <u>http://www.shmj.or.jp/english/pdf/process/exhibi422E.pdf</u>

Version 2022/5/30